

300/566522

Docket No.: 96790P520

IAP20 REGULATIONS 27 JAN 2006

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

YOSHITO JIN, ET AL.

**Art Group:**

Application No.:

**Examiner:**

Filed:

For: BISTABLE RESISTANCE VALUE ACQUISITION DEVICE, MANUFACTURING METHOD THEREOF, METAL OXIDE THIN FILM, AND MANUFACTURING METHOD THEREOF

## **INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of IDS Citation Form PTO/SB/08 or PTO-1449, together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed), which are being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

10/566522

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The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Eric S. Hyman, Reg. No. 30,139

Date: 1/24/06

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<p style="text-align: center;">Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i></p>				<i>Complete if Known</i>			
				Application Number		<b>10/566522</b>	
				Filing Date			
				First Named Inventor		Yoshito Jin	
				Art Unit			
				Examiner Name			
Sheet	1	of	2	Attorney Docket Number	<b>096790 . P520</b>		

<b>U.S.PATENT DOCUMENT</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US 3,795,977		3/12/1974	Berkenflit et al.
		US			
		US			

<b>FOREIGN PATENT DOCUMENT</b>						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Country Code <sup>3</sup>	Number <sup>4</sup>	KindCode <sup>5</sup> (if known)		
		JP	08-031960	A	02-02-1996	MATSUSHITA ELECTRIC IND CO LTD
		JP	10-152397	A	06-09-1998	NIPPON TELEGRAPH & TELEPHONE CORP
		JP	10-152398	A	06-09-1998	NIPPON TELEGR & TELEPH CORP
		JP	2003-077911	A	03-14-2003	NIPPON TELEGR & TELEPH CORP
		JP	2814416	B	08-14-1998	NIPPON TELEGR & TELEPH CORP
		JP	2779997	B	05-15-1998	NIPPON TELEGR & TELEPH CORP
		JP	08-306806	A	11-22-1996	ASAHI CHEM IND CO LTD
		JP	07-263646	A	10-13-1995	MITSUBISHI CHEM CORP
		JP	08-161933	A	06-21-1996	SHARP CORP
		JP	50-004986	A	01-20-1975	INTERNATIONAL BUSINESS MACHINES CORP
		JP	49-034390	B	09-13-1974	MATSUSHITA ELECTRIC IND CO LTD

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov), MPEP901.04 or in the comment box of this document. <sup>3</sup>Enter office that issued the document, by the two-letter code (WIPO Standard ST.3) <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to indicate here if English language Translation is attached.

<p>Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE      STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i></p>				<i>Complete if Known</i> <b>101566522</b>	
				Application Number	
				Filing Date	
				First Named Inventor	Yoshito Jin
				Art Unit	
				Examiner Name	
Sheet	2	of	2	Attorney Docket Number	096790. P520

<b>OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS</b>				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		Translation <sup>2</sup>
		Sze, "Physics of Semiconductor Devices", Jhon Wiley and Sons, Inc., 1981		
		Matsuoka, "Applied Physics", Vol. 73, No. 9, pp.1166, 2004		Abstract
		"Development and Application of Ferroelectric Materials", edited by Tadashi Shiosaki, CMC Co., Ltd.		Abstract
		Inomata et al., "MRM Technology - from Fundamentals to LSI Applications", SIPEC		Abstract
		Amazawa et al., "Ultrathin oxidefilms deposited using electron cyclotron resonance sputter", J. Vac. Sci. Technol., B 17, No. 5		
		Matsuoka et al., "Low-temperature epitaxial growth of BaTiO <sub>3</sub> films by radio-frequency-mode electron cyclotron resonance sputtering", J. Appl. Phys., 76(3), 1768 (1994)		
		Watazu et al., "Powder and Powder Metallurgy", No. 44, pp. 86, 1997		Abstract
		Masumoto et al., "Preparation of Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> films on a single-crystal sapphire substrate with electron cyclotron resonance plasma sputtering", Appl. Phys. Lett., 58, 243 (1991)		
		Yamaguchi et al., "Effect of Grain Size on Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> Thin Film Properties", Jpn. J. Appl. Phys., Vol. 37, (1998) pp. 5166 - 5170		
		Wild et al., "Hafnium and Zirconium silicates for advanced gate dielectrics", J. Appl. Phys., Vol. 87, No. 1, January 2000, pp. 484 - 492		

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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